### Features

- Fast Read Access Time 90 ns
- Dual Voltage Range Operation
  - Unregulated Battery Power Supply Range, 2.7V to 3.6V or Standard 5V  $\pm$  10% Supply Range
- Compatible with JEDEC Standard AT27C020
- Low Power CMOS Operation
  - 20  $\mu\text{A}$  max. (less than 1  $\mu\text{A}$  typical) Standby for V\_{CC} = 3.6V
  - 29 mW max. Active at 5 MHz for  $V_{CC}$  = 3.6V
- Wide Selection of JEDEC Standard Packages
  - 32-Lead PLCC
  - 32-Lead TSOP (8 x 20mm)
  - 32-Lead VSOP (8 x 14mm)
  - 42-Ball CBGA (8 x 8mm)
- High Reliability CMOS Technology
  - 2,000V ESD Protection
  - 200 mA Latchup Immunity
- Rapid<sup>™</sup> Programming Algorithm 100 µs/byte (typical)
- CMOS and TTL Compatible Inputs and Outputs
- JEDEC Standard for LVTTL and LVBO
  Integrated Product Identification Code
- Commercial and Industrial Temperature Ranges

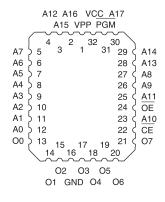
### Description

The AT27BV020 is a high-performance, low-power, low-voltage 2,097,152-bit onetime programmable read only memory (OTP EPROM) organized as 256K by 8 bits. It requires only one supply in the range of 2.7 to 3.6V in normal read mode operation, making it ideal for fast, portable systems using either regulated or unregulated battery power. *(continued)* 

#### **Pin Configurations**

Pin Name	Function
A0 - A17	Address
00 - 07	Outputs
CE	Chip Enable
ŌE	Output Enable
PGM	Program Strobe

#### PLCC, Top View



CBGA Top View

	1	2	3	4	5	6	7	
Α	0	0	0	0	0	$\overline{O}$	0	
	GND	06	VCC	VCC	02	OE	GND	
В	0	$\odot$	$\odot$	$\odot$	$\odot$	$\odot$	$\odot$	
	A17	07	04	NC	NC	00	CE	
С	0	0	0	0	0	0	0	
	A10	NC	05	NC	03	01	A0	
D	0	0	ੁ	0	0	਼ੁ	0	
_	A14	A13	A9	NC	NC	A6	A3	
E	0	<u></u>	<u></u>	्	਼ੁ	਼ੁ	<u></u>	
_	A16	A11	PGM	NC	A7	A4	A1	
F	0	$\odot$	਼ੁ	O.	) VDD	0	0	
	A15	A12	A8	NC	VPP	A5	A2	

#### TSOP, VSOP Top View Type 1

A14  A17  6  5  26    PGM  A17  6  7  26    VPP  A16  10  24    A15  A16  10  22    A7  A6  14  13    A5  A4  16  15	27 25 23 21 19	07 05 03 02 00 A1 A3	06 04 GND 01 A0 A2
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2-Megabit (256K x 8) Unregulated *Battery-Voltage*<sup>™</sup> High Speed OTP EPROM

### AT27BV020

0902A-A-10/97





Atmel's innovative design techniques provide fast speeds that rival 5V parts while keeping the low power consumption of a 3V supply. At  $V_{CC} = 2.7V$ , any byte can be accessed in less than 90 ns. With a typical power dissipation of only 18 mW at 5 MHz and  $V_{CC} = 3V$ , the AT27BV020 consumes less than one fifth the power of a standard 5V EPROM. Standby mode supply current is typically less than 1  $\mu$ A at 3V. The AT27BV020 simplifies system design and stretches battery lifetime even further by eliminating the need for power supply regulation

The AT27BV020 is available in industry standard JEDEC approved one-time programmable (OTP) plastic PLCC, TSOP and VSOP packages, as well as a 42-ball, 1 mm pitch, plastic chip-scale Ball Grid Array package (CBGA). All devices feature two-line control ( $\overline{CE}$ ,  $\overline{OE}$ ) to give designers the flexibility to prevent bus contention.

The AT27BV020 operating with V<sub>CC</sub> at 3.0V produces TTL level outputs that are compatible with standard TTL logic devices operating at V<sub>CC</sub> = 5.0V. At V<sub>CC</sub> = 2.7V, the part is compatible with JEDEC approved low voltage battery operation (LVBO) interface specifications. The device is also capable of standard 5-volt operation making it ideally suited for dual supply range systems or card products that are pluggable in both 3-volt and 5-volt hosts.

Atmel's AT27BV020 has additional features to ensure high quality and efficient production use. The Rapid<sup>™</sup> Program-

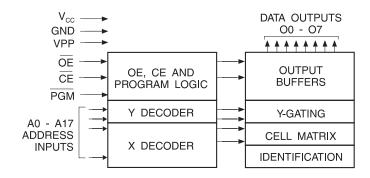
ming Algorithm reduces the time required to program the part and guarantees reliable programming. Programming time is typically only 100  $\mu$ s/byte. The Integrated Product Identification Code electronically identifies the device and manufacturer. This feature is used by industry standard programming equipment to select the proper programming algorithms and voltages. The AT27BV020 programs exactly the same way as a standard 5V AT27C020 and uses the same programming equipment.

#### **System Considerations**

Switching between active and standby conditions via the Chip Enable pin may produce transient voltage excursions. Unless accommodated by the system design, these transients may exceed data sheet limits, resulting in device non-conformance. At a minimum, a 0.1  $\mu$ F high frequency, low inherent inductance, ceramic capacitor should be utilized for each device. This capacitor should be connected between the V<sub>CC</sub> and Ground terminals of the device, as close to the device as possible. Additionally, to stabilize the supply voltage level on printed circuit boards with large EPROM arrays, a 4.7  $\mu$ F bulk electrolytic capacitor should be utilized, again connected between the V<sub>CC</sub> and Ground terminals. This capacitor should be positioned as close as possible to the point where the power supply is connected to the array.

## AT27BV020

### **Block Diagram**



### **Absolute Maximum Ratings\***

Temperature Under Bias40°C to +85°C
Storage Temperature
Voltage on Any Pin with Respect to Ground2.0V to +7.0V <sup>(1)</sup>
Voltage on A9 with Respect to Ground2.0V to +14.0V <sup>(1)</sup>
V <sub>PP</sub> Supply Voltage with Respect to Ground2.0V to +14.0V <sup>(1)</sup>

- \*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
- Note: Minimum voltage is -0.6V DC which may undershoot to 2.0V for pulses of less than 20 ns.Maximum output pin voltage is  $V_{CC}$  + 0.75V DC which may be exceeded if certain precautions are observed (consult application notes) and which may overshoot to +7.0V for pulses of less than 20 ns.

### **Operating Modes**

Mode / Pin	CE	OE	PGM	Ai	V <sub>PP</sub>	V <sub>cc</sub>	Outputs
Read <sup>(2)</sup>	V <sub>IL</sub>	$V_{\rm IL}$	X <sup>(1)</sup>	Ai	Х	$V_{CC}^{(2)}$	D <sub>OUT</sub>
Output Disable <sup>(2)</sup>	Х	V <sub>IH</sub>	Х	Х	Х	V <sub>CC</sub> <sup>(2)</sup>	High Z
Standby <sup>(2)</sup>	V <sub>IH</sub>	Х	Х	Х	Х	V <sub>CC</sub> <sup>(2)</sup>	High Z
Rapid Program <sup>(3)</sup>	V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IL</sub>	Ai	V <sub>PP</sub>	Vcc <sup>(3)</sup>	D <sub>IN</sub>
PGM Verify <sup>(3)</sup>	V <sub>IL</sub>	$V_{\rm IL}$	V <sub>IH</sub>	Ai	V <sub>PP</sub>	V <sub>CC</sub> <sup>(3)</sup>	D <sub>OUT</sub>
PGM Inhibit <sup>(3)</sup>	V <sub>IH</sub>	Х	Х	Х	V <sub>PP</sub>	$V_{CC}^{(3)}$	High Z
Product Identification <sup>(3)(5)</sup>	V <sub>IL</sub>	V <sub>IL</sub>	Х	$\begin{array}{l} A9 = V_{H}^{(4)} \\ A0 = V_{IH} \text{ or } V_{IL} \\ A1 - A17 = V_{IL} \end{array}$	х	V <sub>CC</sub> <sup>(3)</sup>	Identification Code

Notes: 1. X Can be  $V_{IL}$  or  $V_{IH}$ .

2. Read, output disable, and standby modes require, 2.7V  $\leq$  V\_{CC}  $\leq$  3.6V, or 4.5V  $\leq$  V\_{CC}  $\leq$  5.5V.

3. Refer to Programming Characteristics. Programming modes requires  $V_{CC}$  = 6.5V.

- 4.  $V_{H} = 12.0 \pm 0.5 V.$
- 5. Two identifier bytes may be selected. All Ai inputs are held low  $(V_{IL})$ , except A9 which is set to  $V_H$  and A0 which is toggled low  $(V_{IL})$  to select the Manufacturer's Identification byte and high  $(V_{IH})$  to select the Device Code byte.





### DC and AC Operating Conditions for Read Operation

			AT27BV020	
		-90	-12	-15
Operating Temperature (Case)	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C
	Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C
		2.7V to 3.6V	2.7V to 3.6V	2.7V to 3.6V
V <sub>CC</sub> Power Supply		5V ± 10%	5V ± 10%	5V ± 10%
				= Preliminary Information

### DC and Operating Characteristics for Read Operation

Symbol	Parameter	Condition	Min	Max	Units
V <sub>CC</sub> = 2.7V	to 3.6V				
ILI	Input Load Current	$V_{IN} = 0V$ to $V_{CC}$		±1	μA
I <sub>LO</sub>	Output Leakage Current	$V_{OUT} = 0V$ to $V_{CC}$		±5	μA
I <sub>PP1</sub> <sup>(2)</sup>	V <sub>PP</sub> <sup>(1)</sup> Read/Standby Current	$V_{PP} = V_{CC}$		10	μΑ
	V <sup>(1)</sup> Stendley Concert	$I_{SB1}$ (CMOS), $\overline{CE} = V_{CC} \pm 0.3V$		20	μA
I <sub>SB</sub>	Input Load CurrentOutput Leakage Current $V_{PP}^{(1)}$ Read/Standby Current $V_{CC}^{(1)}$ Standby Current $V_{CC}$ Active CurrentInput Low VoltageInput High VoltageOutput Low VoltageOutput Low VoltageOutput Low VoltageInput High VoltageOutput Low VoltageOutput Low VoltageUtput Low VoltageOutput Low VoltageUtput Low VoltageUtput High VoltageUtput High VoltageUtput High VoltageUtput Load CurrentOutput Leakage CurrentV_{PP}^{(1)} Read/Standby CurrentV <sub>CC</sub> (1) Standby Current	$I_{SB2}$ (TTL), $\overline{CE}$ = 2.0 to $V_{CC}$ + 0.5V		100	μA
I <sub>CC</sub>	V <sub>CC</sub> Active Current	f = 5 MHz, $I_{OUT}$ = 0 mA, $\overline{CE}$ = $V_{IL}$ , $V_{CC}$ = 3.6V		8	mA
		V <sub>CC</sub> = 3.0 to 3.6V	-0.6	0.8	V
V <sub>IL</sub>	Input Low Voltage	V <sub>CC</sub> = 2.7 to 3.6V	-0.6	0.2 x V <sub>CC</sub>	V
.,		V <sub>CC</sub> = 3.0 to 3.6V	2.0	V <sub>CC</sub> + 0.5	V
V <sub>IH</sub>	Input High Voltage	V <sub>CC</sub> = 2.7 to 3.6V	0.7 x V <sub>CC</sub>	V <sub>CC</sub> + 0.5	V
		I <sub>OL</sub> = 2.0 mA		0.4	V
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 100 μA		0.2	V
	Output Low Voltage	I <sub>OL</sub> = 20 μA		0.1	V
		I <sub>OH</sub> = -2.0 mA	2.4		V
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -100 μA	V <sub>CC</sub> - 0.2		V
		I <sub>OH</sub> = -20 μA	V <sub>CC</sub> - 0.1		V
V <sub>CC</sub> = 4.5V	to 5.5V				
ILI	Input Load Current	$V_{IN} = 0V$ to $V_{CC}$		±1	μA
I <sub>LO</sub>	Output Leakage Current	$V_{OUT} = 0V \text{ to } V_{CC}$		±5	μA
I <sub>PP1</sub> <sup>(2)</sup>	V <sub>PP</sub> <sup>(1)</sup> Read/Standby Current	$V_{PP} = V_{CC}$		10	μA
	Input Low Voltage      Input High Voltage      Output Low Voltage      Output Low Voltage      Output High Voltage      Output High Voltage      Input Load Current      Output Leakage Current      Output Leakage Current      V <sub>CC</sub> <sup>(1)</sup> Standby Current	$I_{SB1}$ (CMOS), $\overline{CE} = V_{CC} \pm 0.3V$		100	μA
I <sub>SB</sub>	V <sub>CC</sub> <sup>(1)</sup> Standby Current	$I_{SB2}$ (TTL), $\overline{CE}$ = 2.0 to $V_{CC}$ + 0.5V		1	mA
I <sub>CC</sub>	V <sub>CC</sub> Active Current	$f = 5 \text{ MHz}, I_{OUT} = 0 \text{ mA}, \overline{CE} = V_{IL}$		25	mA
V <sub>IL</sub>	Input Low Voltage		-0.6	0.8	V
V <sub>IH</sub>	Input High Voltage		2.0	V <sub>CC</sub> + 0.5	V
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 2.1 mA		0.4	V
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -400 μA	2.4		V

Notes: 1.  $V_{CC}$  must be applied simultaneously with or before  $V_{PP}$  and removed simultaneously with or after  $V_{PP}$ 

2.  $V_{PP}$  may be connected directly to  $V_{CC}$ , expect during programming. The supply current would then be the sum of  $I_{CC}$  and  $I_{PP}$ 

# AT27BV020

### **AC Characteristics for Read Operation**

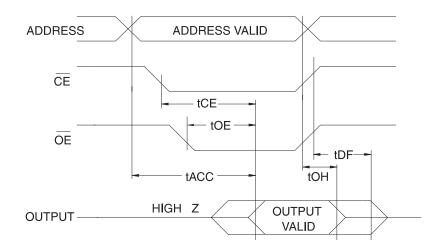
(V<sub>CC</sub> = 2.7V to 3.6V and 4.5V to 5.5V)

			AT27BV020						
			-9	90		-12 -15		15	
Symbol	Parameter	Condition	Min	Мах	Min	Max	Min	Max	Units
t <sub>ACC</sub> <sup>(3)</sup>	Address to Output Delay	$\overline{CE} = \overline{OE} = V_{IL}$		90		120		150	ns
t <sub>CE</sub> <sup>(2)</sup>	CE to Output Delay	$\overline{OE} = V_{IL}$		90		120		150	ns
t <sub>OE</sub> <sup>(2)(3)</sup>	OE to Output Delay	$\overline{CE} = V_{IL}$		50		50		60	ns
t <sub>DF</sub> <sup>(4)(5)</sup>	OE or CE High to Output Float, whichever occurred first			40		40		50	ns
t <sub>OH</sub>	Output Hold from Address, $\overline{CE}$ or $\overline{OE}$ , whichever occurred first		0		0		0		ns

Note: 2,3,4,5. - see AC Waveforms for Read Operation

= Preliminary Information

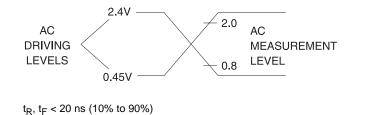
### AC Waveforms for Read Operation<sup>(1)</sup>



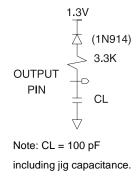
- Notes: 1. Timing measurement references are 0.8V and 2.0V. Input AC drive levels are 0.45V and 2.4V, unless otherwise specified.
  - 2.  $\overline{OE}$  may be delayed up to t<sub>CE</sub> t<sub>OE</sub> after the falling edge of  $\overline{CE}$  without impact on t<sub>CE</sub>.
  - 3.  $\overline{\text{OE}}$  may be delayed up to  $t_{ACC}$   $t_{OE}$  after the address is valid without impact on  $t_{ACC}$ .
  - 4. This parameter is only sampled and is not 100% tested.
  - 5. Output float is defined as the point when data is no longer driven.



### Input Test Waveform and Measurement Level



**Output Test Load** 

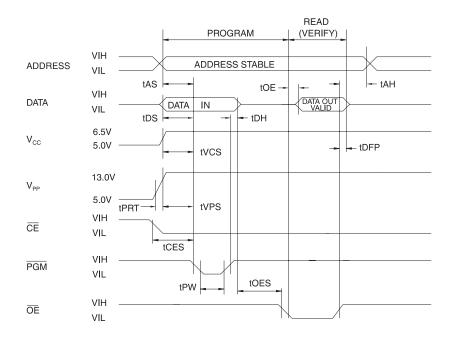


# **Pin Capacitance**<sup>(1)</sup> (f = 1 MHz, T = $25^{\circ}$ C)

	Тур	Мах	Units	Conditions
C <sub>IN</sub>	4	8	pF	$V_{IN} = 0V$
C <sub>OUT</sub>	8	12	pF	$V_{OUT} = 0V$

Typical values for nominal supply voltage. This parameter is only sampled and is not 100% tested. Note:

### **Programming Waveforms**<sup>(1)</sup>



- Notes: 1. The Input Timing Reference is 0.8V for  $\rm V_{IL}$  and 2.0V for  $\rm V_{IH}.$ 
  - 2.  $t_{OE}$  and  $t_{DFP}$  are characteristics of the device but must be accommodated by the programmer.
  - 3. When programming the AT27BV020 a 0.1  $\mu$ F capacitor is required across V<sub>PP</sub> and ground to suppress spurious voltage transients.

### **DC Programming Characteristics**

 $T_A = 25 \pm 5^{\circ}C, V_{CC} = 6.5 \pm 0.25V, V_{PP} = 13.0 \pm 0.25V$ 

			Li	Limits			
Symbol	Parameter	Test Conditions	Min	Max	Units		
ILI	Input Load Current	$V_{IN} = V_{IL}, V_{IH}$		±10	μA		
V <sub>IL</sub>	Input Low Level		-0.6	0.8	V		
V <sub>IH</sub>	Input High Level		2.0	V <sub>cc</sub> + 0.5	V		
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 2.1 mA		0.4	V		
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -400 μA	2.4		V		
I <sub>CC2</sub>	V <sub>CC</sub> Supply Current (Program and Verify)			40	mA		
I <sub>PP2</sub>	V <sub>PP</sub> Supply Current	$\overline{CE} = \overline{PGM} = V_{IL}$		20	mA		
V <sub>ID</sub>	A9 Product Identification Voltage		11.5	12.5	V		





### **AC Programming Characteristics**

 $T_A = 25 \pm 5^{\circ}C, V_{CC} = 6.5 \pm 0.25V, V_{PP} = 13.0 \pm 0.25V$ 

	Test Conditions <sup>(1)</sup>		Lir		
Symbol	Parameter	AC Conditions of Test	Min	Max	Units
t <sub>AS</sub>	Address Setup Time		2		μs
t <sub>CES</sub>	CE Setup Time		2		μs
t <sub>OES</sub>	OE Setup Time	Input Rise and Fall Times (10% to 90%) 20ns	2		μs
t <sub>DS</sub>	Data Setup Time		2		μs
t <sub>AH</sub>	Address Hold Time	Input Pulse Levels	0		μs
t <sub>DH</sub>	Data Hold Time	0.45V to 2.4V	2		μs
t <sub>DFP</sub>	OE High to Output Float Delay <sup>(3)</sup>	Input Timing Reference Level	0	130	ns
t <sub>VPS</sub>	V <sub>PP</sub> Setup Time	0.8V to 2.0V	2		μs
t <sub>VCS</sub>	V <sub>CC</sub> Setup Time		2		μs
t <sub>PW</sub>	<b>PGM</b> Program Pulse Width <sup>(2)</sup>	Output Timing Reference Level 0.8V to 2.0V	95	105	μs
t <sub>OE</sub>	Data Valid from OE			150	ns
t <sub>PRT</sub>	V <sub>PP</sub> Pulse Rise Time During Programming		50		ns

Notes: 1.  $V_{CC}$  must be applied simultaneously or before  $V_{PP}$  and removed simultaneously or after  $V_{PP}$ 

- 2. This parameter is only sampled and is not 100% tested. Output Float is defined as the point where data is no longer driven —see timing diagram.
- 3. Program Pulse width tolerance is 100  $\,\mu\text{sec}\pm5\%.$

### Atmel's 27BV020 Integrated Product Identification Code<sup>(1)</sup>

		Pins								
Codes	A0	07	06	O5	04	O3	02	01	00	Data
Manufacturer	0	0	0	0	1	1	1	1	0	1E
Device Type	1	1	0	0	0	0	1	1	0	86

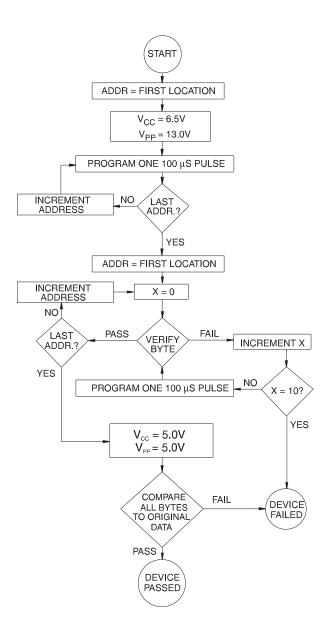
Note: The AT27BV020 has the same Product Identification Code as the AT27C020. Both are programming compatible.

AT27BV020

#### **Rapid Programming Algorithm**

A 100  $\mu$ s PGM pulse width is used to program. The address is set to the first location. V<sub>CC</sub> is raised to 6.5V and V<sub>PP</sub> is raised to 13.0V. Each address is first programmed with one 100  $\mu$ s PGM pulse without verification. Then a verification/reprogramming loop is executed for each address. In the event a byte fails to pass verification, up to 10 successive 100  $\mu$ s pulses are applied with a verification after each pulse. If the byte fails to verify after 10 pulses

have been applied, the part is considered failed. After the byte verifies properly, the next address is selected until all have been checked.  $V_{PP}$  is then lowered to 5.0V and  $V_{CC}$  to 5.0V. All bytes are read again and compared with the original data to determine if the device passes or fails.





### **Ordering Information**

t <sub>ACC</sub> (ns)	I <sub>CC</sub> (mA) V <sub>CC</sub> = 3.6V				
	Active	Standby	Ordering Code	Package	<b>Operation Range</b>
90	8	0.02	AT27BV020-90CC	42C	Commercial
			AT27BV020-90JC	32J	(0°C to 70°C)
			AT27BV020-90TC	32T	
			AT27BV020-90VC	32V	
	8	0.02	AT27BV020-90CI	42C	Industrial
			AT27BV020-90JI	32J	(-40°C to 85°C)
			AT27BV020-90TI	32T	
			AT27BV020-90VI	32V	
120	8	0.02	AT27BV020-12CC	42C	Commercial
			AT27BV020-12JC	32J	(0°C to 70°C)
			AT27BV020-12TC	32T	
			AT27BV020-12VC	32V	
	8	0.02	AT27BV020-12CI	42C	Industrial
			AT27BV020-12JI	32J	(-40°C to 85°C)
			AT27BV020-12TI	32T	
			AT27BV020-12VI	32V	
150	8	0.02	AT27BV020-15CC	42C	Commercial
			AT27BV020-15JC	32J	(0°C to 70°C)
			AT27BV020-15TC	32T	
			AT27BV020-15VC	32V	
	8	0.02	AT27BV020-15CI	42C	Industrial
			AT27BV020-15JI	32J	(-40°C to 85°C)
			AT27BV020-15TI	32T	
			AT27BV020-15VI	32V	

= Preliminary Information

Package Type				
42C	42-Ball, Plastic Chip-Scale Ball Grid Array (CBGA) (8 x 8mm)			
32J	32-Lead, Plastic J-Leaded Chip Carrier (PLCC)			
32T	32-Lead, Plastic Thin Small Outline Package (TSOP) (8 x 20mm)			
32V	32-Lead, Plastic Thin Small Outline Package (VSOP) (8 x 14mm)			

# AT27BV020